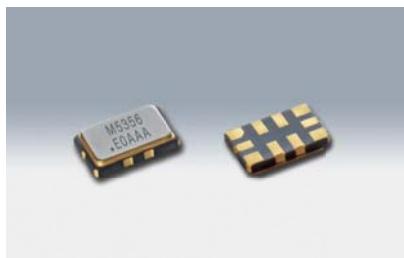


TC-MO / VC TC-MO - Super Low Jitter

MO5155/MO5156/MO5157/MO5356/MO5357/MO5358/MO5359



■ Features

- 5.0×3.2 mm Ceramic package
- LVC MOS or Clipped Sinewave output

■ Applications

- Synchronous Ethernet
- Small cell
- Optical transport-SONET/SDH, OTN
- IEEE1588
- Test and measurement



Model	Output Frequency (MHz)	Frequency Tolerance ($\times 10^{-6}$)	Supply Voltage (V)	Current Consumption (mA Typ.)	Size (mm)	Output		
MO5155	10 std. GNSS Freq.	$\pm 0.5, \pm 1.0, \pm 2.5$	+2.25 to +3.63	+40 to +50	5.0×3.2×0.95 (Ceramic)	Clipped Sinewave (1 to 60 MHz) LVC MOS		
MO5156	1 to 60							
MO5157	60 to 220							
MO5356	1 to 60							
MO5357	60 to 220		±0.1, ±0.2, ±0.25			Clipped sinewave, LVC MOS		
MO5358	1.0 to 60							
MO5359	60 to 189, 200 to 220							

■ Standard Specification (MO5356)

Item	Legend	Min.	Typ.	Max.	Unit	Condition
Output Frequency Range	f	1	-	60	MHz	
Supply Voltage	Vdd	+2.25	+2.50	+2.75	V	
		+2.52	+2.80	+3.08		
		+2.70	+3.00	+3.30		
		+2.97	+3.30	+3.63		
Operating Temperature Range	T_use	-20	-	+70	°C	Extended commercial
		-40	-	+85		Industrial
		-40	-	+105		Extended Industrial, ambient temperature
Initial Tolerance	F_init	-1.0	-	+1.0	$\times 10^{-6}$	Inclusive of solder-down shift at 48 hours after 2 reflows at +25°C
Frequency Stability over temperature	F_stab	-0.10	-	+0.10	$\times 10^{-6}$	Referenced to (fmas + fmin)/2 over the specified temperature range
		-0.20	-	+0.20		
		-0.25	-	+0.25		
First Year Aging	F_aging1	-	±1.0	-	$\times 10^{-6}$	$T_A = +25^\circ\text{C}$
Pull Range	PR	±6.25		$\times 10^{-6}$	VC TC-MO mode. Contact KDS for $\pm 12.5, \pm 25$	
		$\pm 6.25, \pm 10, \pm 12.5, \pm 25, \pm 50, \pm 80, \pm 100, \pm 125, \pm 150, \pm 200, \pm 400, \pm 600, \pm 800, \pm 1200, \pm 1600, \pm 3200$		$\times 10^{-6}$	DC TC-MO mode.	
Upper Control Voltage	VC_U	Vdd×0.9	-	-	V	
Control Voltage Range	VC_L	-	-	Vdd×0.1	V	
Control Voltage Input Impedance	VC_z	8	-	-	MΩ	
Control Voltage Input Bandwidth	VC_c	-	10	-	KHz	
Frequency Change Polarity	-	Positive Slope		-		
Current Consumption	Idd	-	+44	+53	mA	No load condition, f = 19.2 MHz, TC-MO and DC TC-MO mode.
		-	+48	+57		No load condition, f = 19.2 MHz, VC TC-MO mode.
OE Disable Current	I_od	-	+43	+51	mA	OE = GND, output is weakly pull down, TC-MO and DC TC-MO mode.
		-	+47	+55		OE = GND, output is weakly pull down, VC TC-MO mode.
Input Low Voltage	V _{IL}	-	-	Vdd×0.3	V	For OE pin
Input High Voltage	V _{IH}	Vdd×0.7	-	-	V	For OE pin
Start-up Time	T_start	-	2.5	3.5	ms	Time to first pulse, Measured from the time Vdd reaches its rated minimum value.
RMS Period Jitter	T_jitt	-	0.8	1.1	ps	f = 10 MHz
LVC MOS Output						
Duty Cycle	DC	45	-	55	%	
Output Low Voltage	V _{OL}	-	-	Vdd×0.1	V	I _{OL} = -3mA
Output High Voltage	V _{OH}	Vdd×0.9	-	-	V	I _{OH} = +3 mA
Rise and Fall Time	Tr, Tf	0.8	1.2	1.9	ns	10% to 90% Vdd.
RMS Phase Jitter (random)	T_phj	-	0.31	0.48	ps	f = 50 MHz, Integration bandwidth = 12 kHz to 20 MHz, -40 to +85 °C
Clipped Sinewave Output						
Output Voltage Level	Vout	+0.8	-	+1.2	%	10kΩ 10pF ± 10%
Rise and Fall Time	Tr, Tf	-	3.5	4.6	V	20% to 80% Vdd, 19.2MHz
RMS Phase Jitter (random)	T_phj	-	0.31	0.48	ps	f = 60 MHz, Integration bandwidth = 12 kHz to 20 MHz, -40 to +85 °C
Packing Unit	1000pcs./reel (φ 180)					